

T-33-29

8961726 TEXAS INSTR (OPTO)

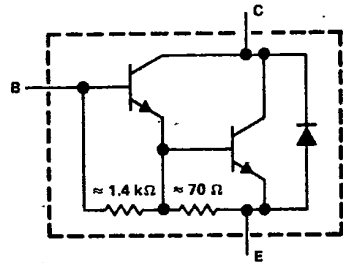
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**BDX53, BDX53A, BDX53B, BDX53C
N-P-N SILICON POWER DARLINGTONS**

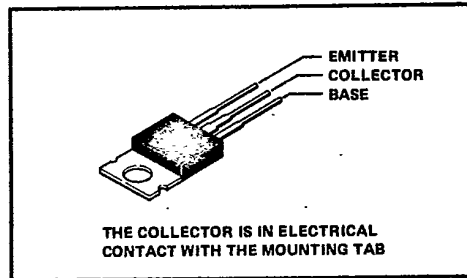
REVISED OCTOBER 1984

- 60 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Min h_{FE} of 750 at 3 V, 3 A

device schematic



TO-220AB PACKAGE



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

| | BDX53 | BDX53A | BDX53B | BDX53C |
|------------------------------------------------------------------------------------|-----------------|--------|--------|--------|
| Collector-base voltage | 45 V | 60 V | 80 V | 100 V |
| Collector-emitter voltage ($I_B = 0$) | 45 V | 60 V | 80 V | 100 V |
| Emitter-base voltage | 5 V | | | |
| Continuous collector current | 8 A | | | |
| Continuous base current | 200 mA | | | |
| Continuous device dissipation at (or below) 25°C case temperature (see Note 1) | 60 W | | | |
| Continuous device dissipation at (or below) 25°C free-air temperature (see Note 2) | 2 W | | | |
| Operating free-air temperature range | - 65°C to 150°C | | | |
| Operating collector junction and storage temperature range | - 65°C to 150°C | | | |

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.48 W/°C.
2. Derate linearly to 150°C free-air temperature at the rate of 16 mW/°C.

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BD, BDW, BDX, BU, BUX, BUY Devices

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N-P-N SILICON POWER DARLINGTONS**

electrical characteristics at 25°C case temperature

| PARAMETER | TEST CONDITIONS | BDX53 | | | BDX53A | | | BDX53B | | | BDX53C | | | UNIT |
|---------------|---------------------------------------------------------------------|-------|-----|-----|--------|-----|-----|--------|-----|-----|--------|-----|-----|---------------|
| | | MIN | TYP | MAX | MIN | TYP | MAX | MIN | TYP | MAX | MIN | TYP | MAX | |
| $V_{(BR)CEO}$ | $I_C = 100 \text{ mA}$, $I_B = 0$, See Note 3 | 45 | | | 60 | | | 80 | | | 100 | | | V |
| I_{CEO} | $V_{CE} = 30 \text{ V}$, $I_B = 0$ | | 500 | | | 500 | | | | 500 | | | | μA |
| | $V_{CE} = 40 \text{ V}$, $I_B = 0$ | | | | | | | | | | | | | |
| | $V_{CE} = 50 \text{ V}$, $I_B = 0$ | | | | | | | | | | | | 500 | |
| I_{CBO} | $V_{CB} = 45 \text{ V}$, $V_{BE} = 0$ | | 200 | | | | | | | | | | | μA |
| | $V_{CB} = 60 \text{ V}$, $V_{BE} = 0$ | | | | | 200 | | | | | | | | |
| | $V_{CB} = 80 \text{ V}$, $V_{BE} = 0$ | | | | | | | | 200 | | | | | |
| | $V_{CB} = 100 \text{ V}$, $V_{BE} = 0$ | | | | | | | | | | | 200 | | |
| I_{EBO} | $V_{EB} = 5 \text{ V}$, $I_C = 0$ | | 2 | | | 2 | | | 2 | | | 2 | | mA |
| h_{FE} | $V_{CE} = 3 \text{ V}$, $I_C = 3 \text{ A}$, See Notes 3 and 4 | 750 | | | 750 | | | 750 | | | 750 | | | |
| $V_{BE(sat)}$ | $I_C = 3 \text{ A}$, $I_B = 12 \text{ mA}$, See Notes 3 and 4 | | 2.5 | | | 2.5 | | | 2.5 | | | 2.5 | | V |
| $V_{CE(sat)}$ | $I_C = 3 \text{ A}$, $I_B = 12 \text{ mA}$, See Notes 3 and 4 | | 2 | | | 2 | | | 2 | | | 2 | | V |
| V_F | $I_F = 3 \text{ A}$ | | 2.5 | | | 2.5 | | | 2.5 | | | 2.5 | | V |

NOTES: 3. These parameters must be measured using pulse techniques, $t_W = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

4. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3.2 mm (0.125 inch) from the device body.

thermal characteristics

| PARAMETER | MIN | TYP | MAX | UNIT |
|-----------------|-----|-----|------|----------------------|
| $R_{\theta JC}$ | | | 2.08 | |
| $R_{\theta JA}$ | | | 62.5 | $^{\circ}\text{C/W}$ |

resistive-load switching characteristics at 25°C case temperature

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------|------------------------------------------------------------------------------|-----|-----|-----|---------------|
| t_{on} | $I_C = 3 \text{ A}$, $I_{B1} = 12 \text{ mA}$, $I_{B2} = -12 \text{ mA}$, | | 1 | | |
| t_{off} | $V_{BE(off)} = -4.5 \text{ V}$, $R_L = 10 \Omega$, See Figure 1 | | 5 | | μs |

BD, BDW, BDX, BU, BUX, BUY Devices

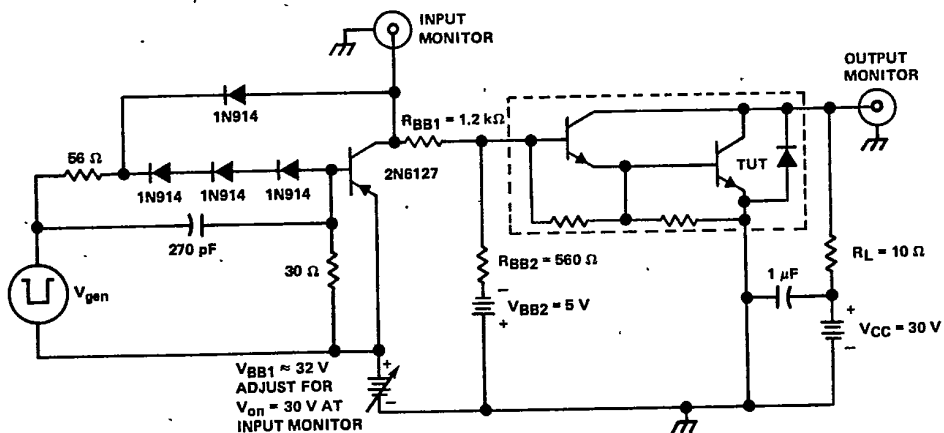
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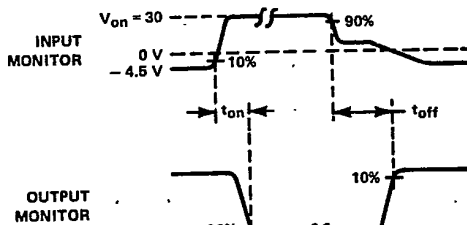
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PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE WAVEFORMS

- NOTES:
- A. V_{gen} is a -30-V pulse into a $50\ \Omega$ termination.
 - B. The V_{gen} waveform is supplied by a generator with the following characteristics: $t_r < 15\text{ ns}$, $t_f < 15\text{ ns}$, $Z_{out} = 50\ \Omega$, $t_w = 20\ \mu\text{s}$, duty cycle $\leq 2\%$.
 - C. Waveforms are monitored on an oscilloscope with the following characteristics: $t_r < 15\text{ ns}$, $R_{in} \geq 10\text{ M}\Omega$, $C_{in} < 11.5\text{ pF}$.
 - D. Resistors must be noninductive types.
 - E. The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1. RESISTIVE-LOAD SWITCHING

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TYPICAL CHARACTERISTICS

STATIC FORWARD CURRENT TRANSFER RATIO vs COLLECTOR CURRENT

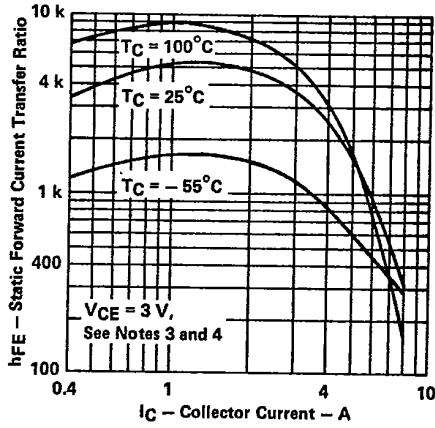


FIGURE 2

BASE-EMITTER VOLTAGE vs CASE TEMPERATURE

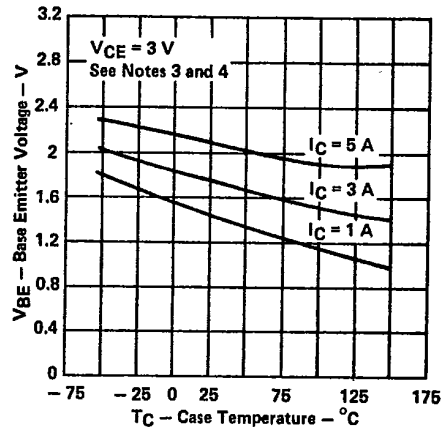


FIGURE 3

COLLECTOR-EMITTER SATURATION VOLTAGE vs CASE TEMPERATURE

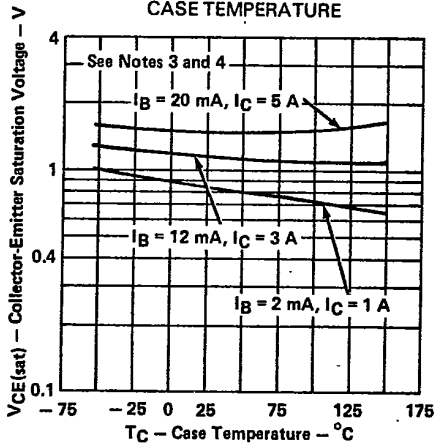


FIGURE 4

SMALL SIGNAL COMMON-EMITTER FORWARD CURRENT TRANSFER RATIO vs FREQUENCY

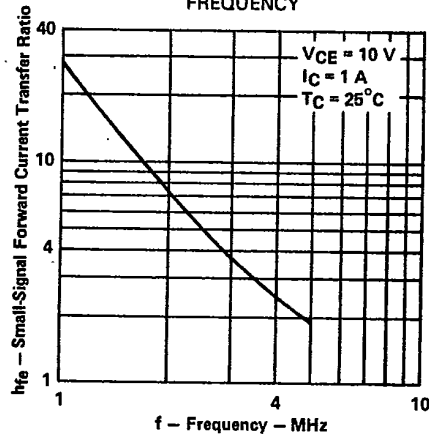


FIGURE 5

- NOTES:**
3. These parameters must be measured using pulse techniques, $t_W = 300 \mu s$, duty cycle $\leq 2\%$.
 4. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3.2 mm (0.125 inch) from the device body.



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MAXIMUM SAFE OPERATING AREA

MAXIMUM COLLECTOR CURRENT
vs
COLLECTOR-EMITTER VOLTAGE

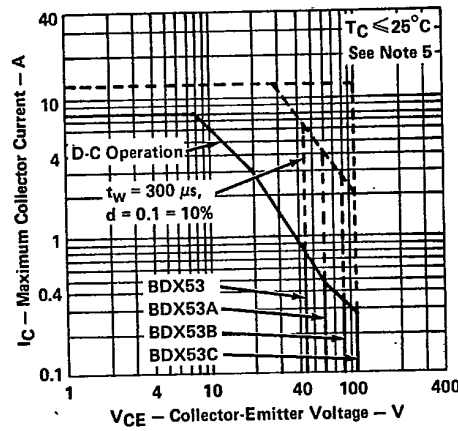


FIGURE 6

NOTE 5: This combination of maximum voltage and current may be achieved only when switching from saturation to cutoff with a clamped inductive load.

THERMAL INFORMATION

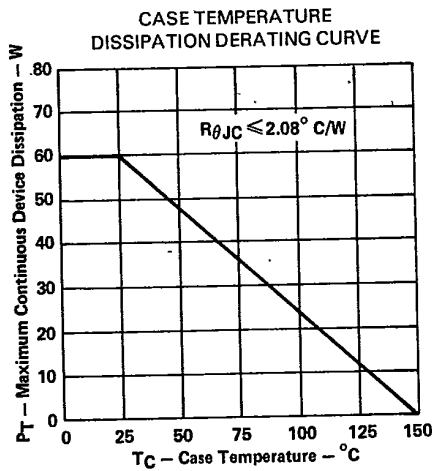


FIGURE 7

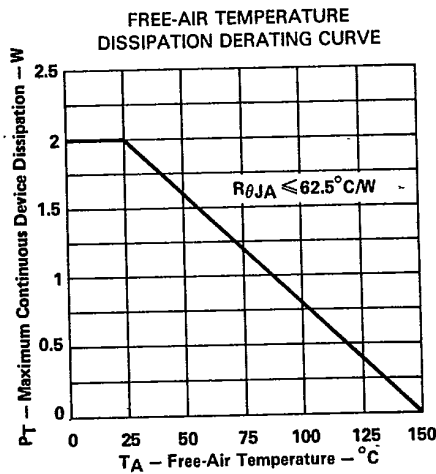


FIGURE 8



BD, BDW, BDX, BU, BUX, BUY Devices